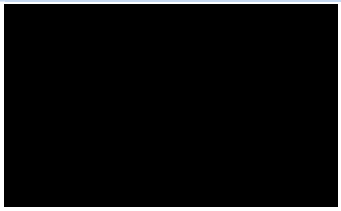
SOP-8 ĮĮ Ŀ Ŭ ´ ɯ Ą ₩ Ã MOS ʃ ̃ Ẓ ˥

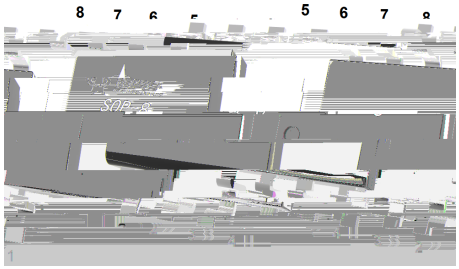
Complementary Enhancement MOSFET in a SOP-8 Plastic Package.

N-channel	P-channel
V_{DS}(V)=40V	V_{DS}(V)=-40V
I_D=8A(T_C=25 ł)	I_D=-7A(T_C=25 ł)
$U_{GV+RQ,}$?58 p Ƒ+Y JV@43Y,	$U_{GV+RQ,}$?68 p Ƒ+Y JV@043Y,
$U_{GV+RQ,}$?78 p Ƒ+Y JV@718Y,	$U_{GV+RQ,}$?93 p Ƒ+Y JV@0718Y,
ƞ ғ β HF Product.	

ĸ ɤ ı ' GF2GF ɕ Ω ⊐ ı ' Ã ʜ ی ĸ Ă ق ɔ Ã ʜ ð ǐ Ķ ɔ ˙ Ẓ ғ

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies. And suitable for use as a load switch or in PWM applications.





PIN1 χ S1 PIN 2 χ G1 PIN 3 χ S2 PIN 4 χ G2
PIN 5 χ D2 PIN 6 χ D2 PIN 7 χ D1 PIN 8 χ D1

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See Marking Instructions.

v ̈Ω Parameter	ϒ N Symbol		̈Ω Ö Rating		D Ђ Unit
			N-channel	P-channel	
Drain-Source Voltage	V_{DSS}		40	-40	V
Gate-Source Voltage	V_{GSS}		±20		V
Continuous Drain Current	I_D (T_C=25)		8	-7	A
Continuous Drain Current	I_D (T_A=25)		6	-5	A
Pulsed Drain Current	I_{DM}		20	-20	A
Power Dissipation	P_D (T_C=25)		3.5	3.5	W
Power Dissipation	P_D (T_A=25)		2	2	W
Maximum Junction-to-Ambient	$R_{\theta JA}$	t ≤ 10s	62.5		/W
	$R_{\theta JA}$	Steady-State	110		/W
Maximum Junction-to-Case	$R_{\theta JC}$	Steady-State	35.7		/W
Junction and Storage Temperature Range	T_J,T_{STG}		-55 to +150		

N-

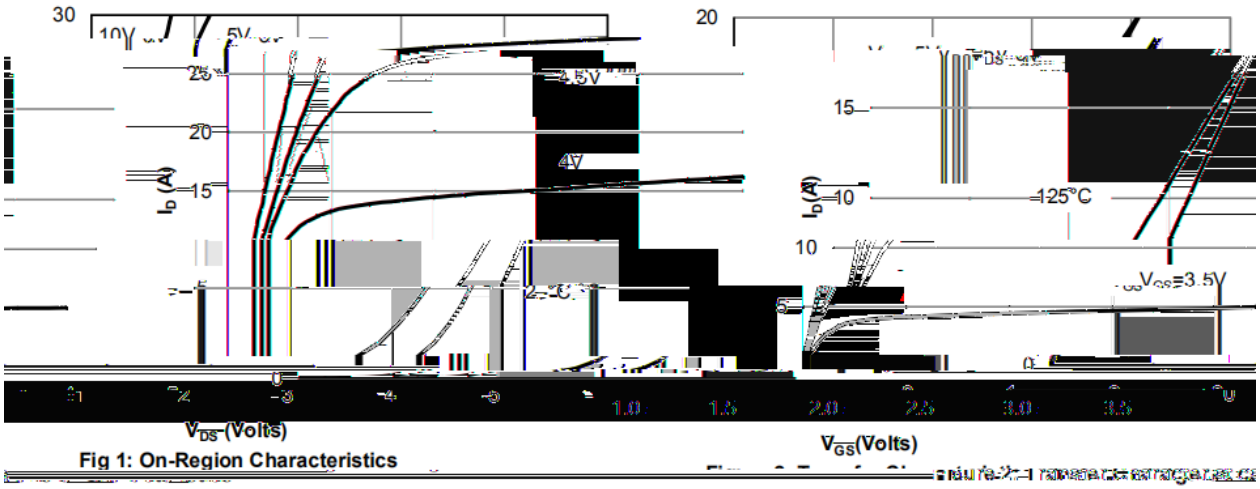
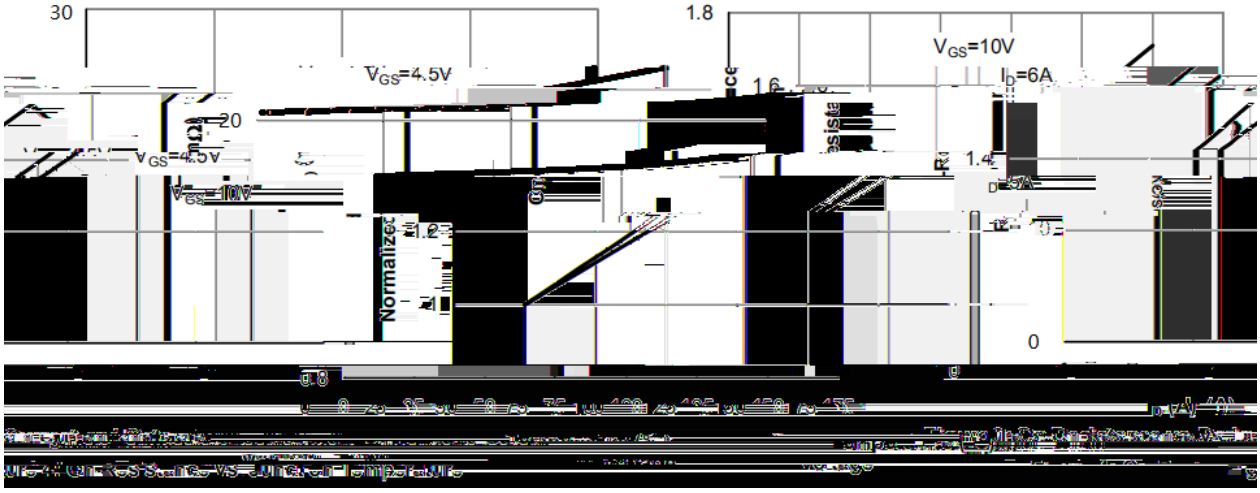
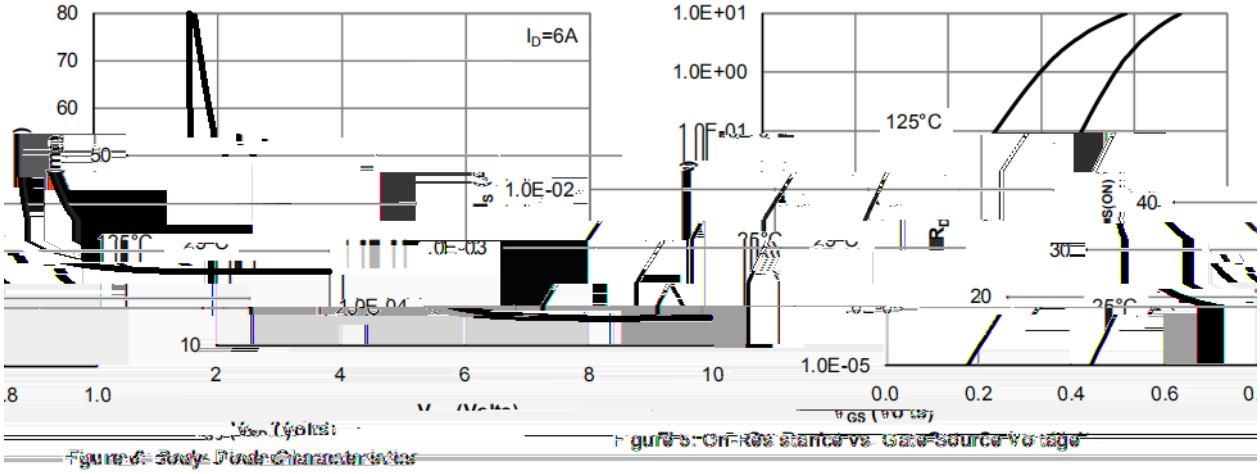


Fig 1: On-Region Characteristics





v ̈Ω Parameter	ϒ N Symbol	⅄ ;↑ ϯ Test Conditions	ѡ ṇ Ө Min	Ɛ ʒ Ө Typ	ѡ ᶻ Ө Max	ɒ ɟ Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-40	-46		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-40V V_{GS}=0V			-1.0	μA
		V_{DS}=-40V V_{GS}=0V T_J=55			-5.0	μA
Gate-Body leakage current	I_{GSS}	V_{GS}=±20V V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=-250μA	-1.4	-1.6	-3.0	V
On state drain current	$I_{D(on)}$	V_{DS}=-5V V_{GS}=-10V	6			A
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V I_D=-5.0A		32	35	mΩ
		V_{GS}=-4.5V I_D=-2.0A		49	60	mΩ
Forward Transconductance	g_{FS}	V				

P-

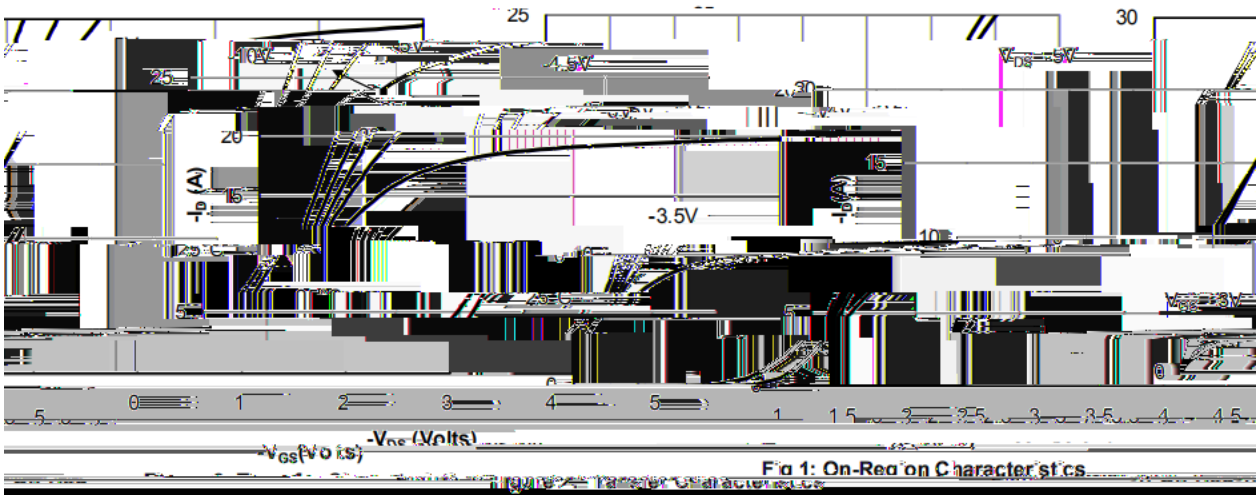
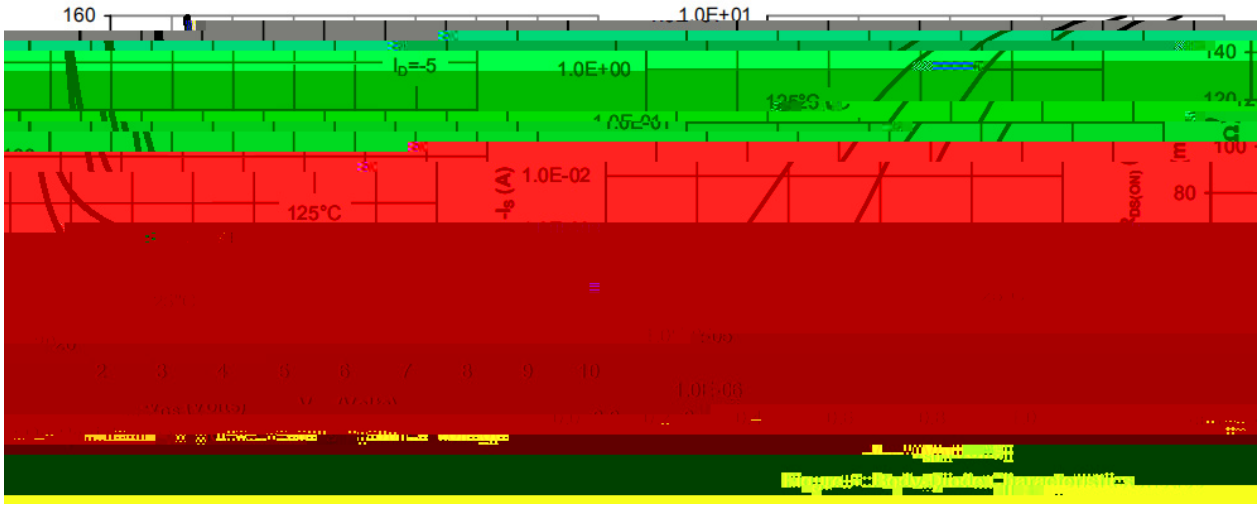


Fig 1: On-Region Characteristics





P-

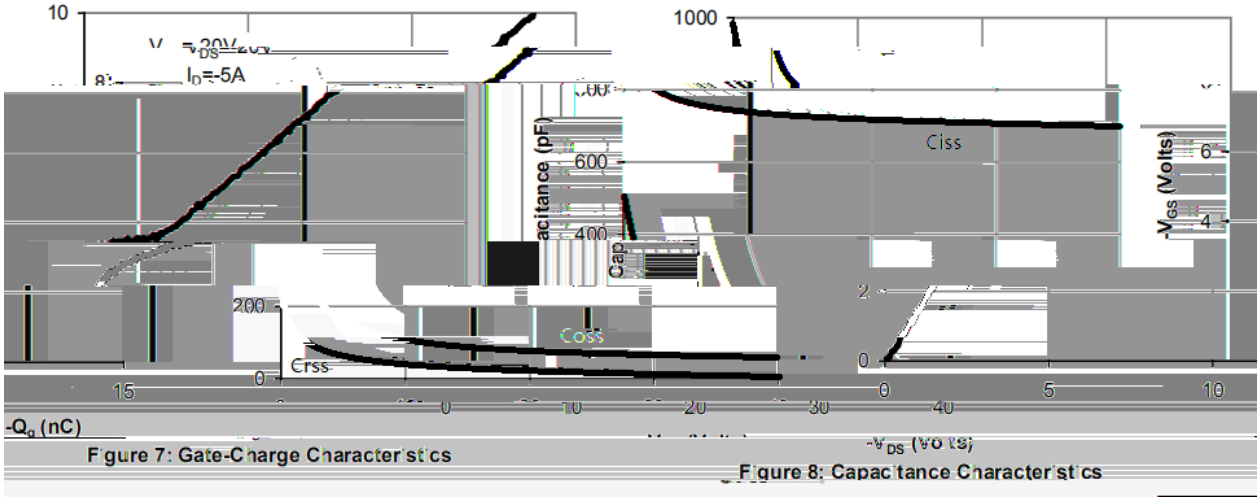
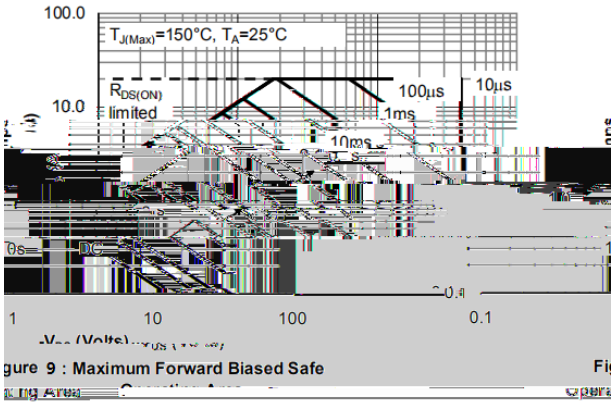
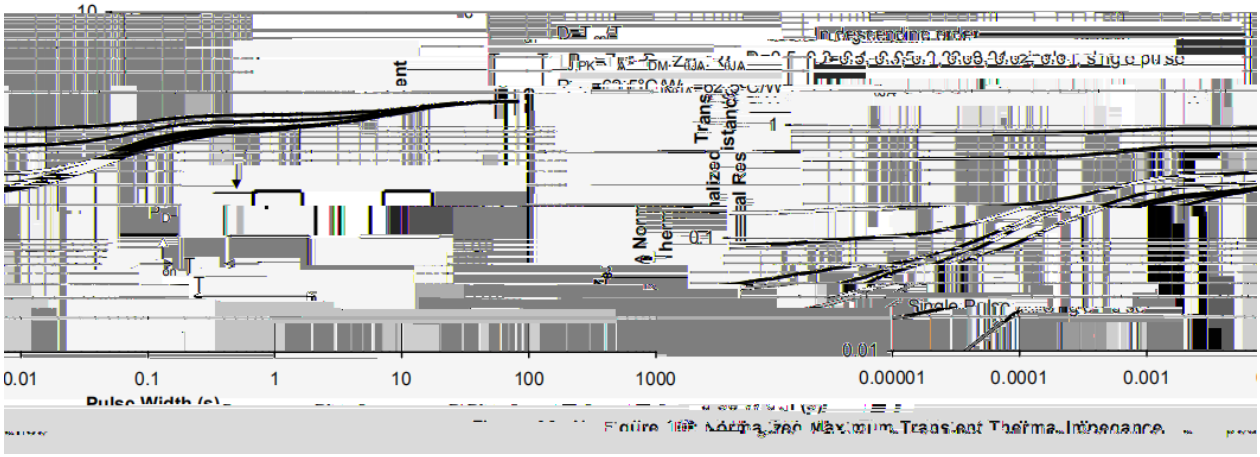


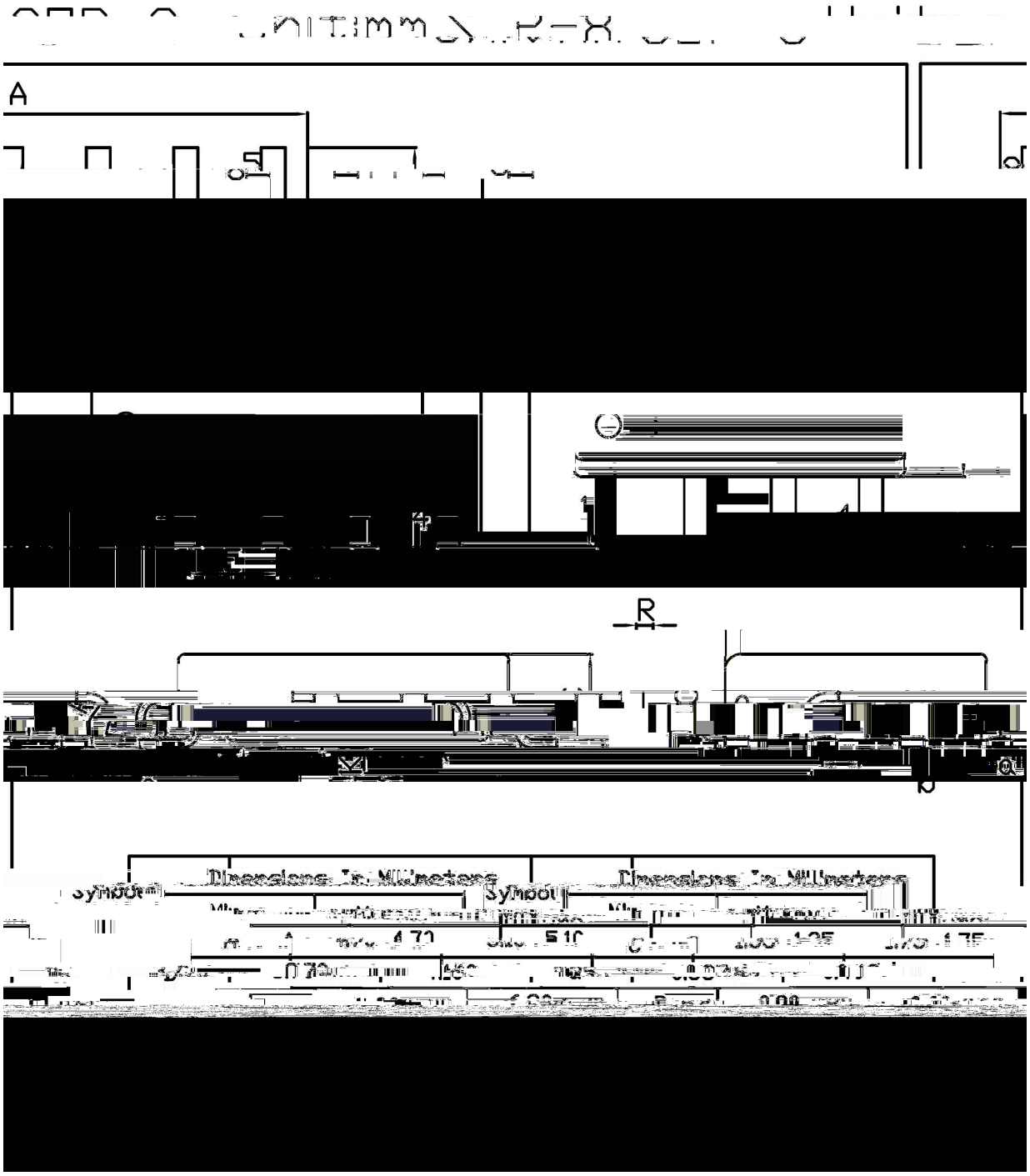
Figure 7: Gate-Charge Characteristics

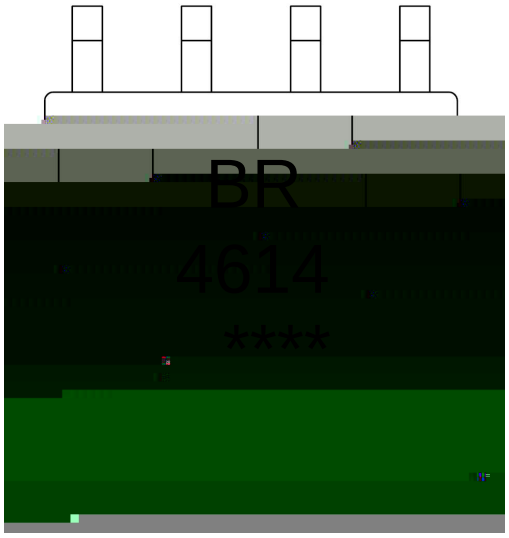
Figure 8: Capacitance Characteristics



gure 9 : Maximum Forward Biased Safe




A
R
Dimensions In Millimeters
Symbol
Dimensions In Millimeters
Symbol



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Note:

BR:	Company Code
4614:	Product Type Code
****:	Lot No. Code, code change with Lot No